

Smooth High at% Silicon SiCH and Ultra-thin SiCH Capsules

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IFTNP2024-015



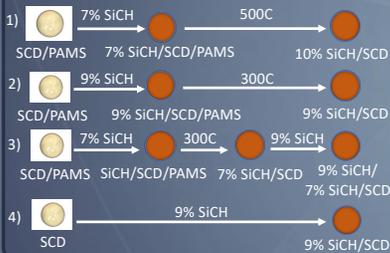
Experimental Objective

SiCH Capsule Goal: Smooth, cryo-quality, multilayered capsule with at least 9at% Si outer layer and SCD (strong CD) inner layer.

Reason: Enable mapping of high silicon content CH layers (>7at% Si) to determine optimum Si content for maximum yield at shot time.

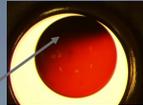
Side Goal: Determined thinnest free-standing capsule that can be produced.

Four Routes for High Si Content SiCH/SCD Capsule Explored

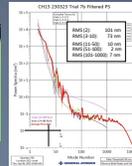


Method 1 - Pyro of 7% SiCH/SCD at 500C under N2

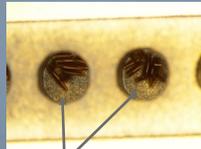
SiCH layer (10+ at% Si) after pyrolysis SCD almost disappears.



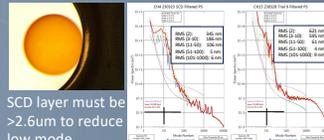
Method 3 - 1.3µm 7% Si on 2.3µm SCD pre-PAMS; 1.6µm 9% Si deposited on SiCH/SCD post-PAMS



Method 2 - 9+% Si on thin SCD pre-PAMS removal not viable



Method 4 - Deposit 9% SiCH onto 2.6µm SCD capsule after PAMS pyro somewhat successful



SCD layer must be >2.6µm to reduce low mode roughness

High aspect ratio silicon doped GDP (6at% Si) have higher buckle pressure than un-doped GDP or SCD

Batch	OD (µm)	Wall (µm)	Survive 15 psia buckle	Survive 30 psia buckle	Youngs Modulus E (Gpa)
CH15-340526	~3100	6.5	No		<4.9
CH2-110815	~3150	8.8	Yes	No	>2.7 <5.4
CH2-100215	~3200	10.1	Yes	Yes	>4.0

Normal GDP expected buckle pressure (max) for 3150x8.8 µm 10.5 PSI
SCD expected buckle pressure (max) for 3150x8.8 µm 15.5PSI
E (normal GDP) = 1.9 Gpa
E (SCD) = 2.4 Gpa

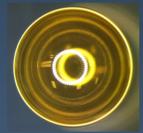


Superior buckle pressure allows for 3mm CFTA builds with capsules having <10µm wall thickness

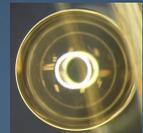
3.1mmx6.5µm SiCH (5at% Si) pre 1 atm buckle test



3.15mmx8.8µm SiCH (6at% Si) capsule after 1 atm buckle test



3.2mmx10.1µm SiCH (6at% Si) capsule after 2 atm buckle test



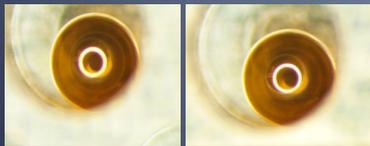
Capsules survived 20C → LN₂ → 20C temperature cycle test

Type 3

Type 3 Buckle Strength

OD (µm)	Outer SiCH 9at% Si (µm)	Inner SiCH 6at% Si (µm)	Inner SCD (µm)	Total Wall (µm)	B. Pres. PSI	Youngs Modulus E (Gpa)
935	3.7	1.0	1.9	6.6	117	3.49
936	3.7	1.0	1.9	6.6	104	3.06

Note: For reference: E (SCD) = 2.4 Gpa



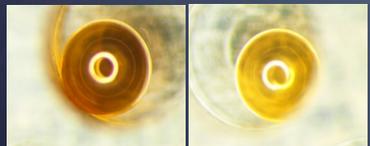
Batch 1 SiCH/SiCH/SCD 9%; 6-7%
Batch 2 SiCH/SiCH/SCD 9%; 6-7%

Type 4

Type 4 Buckle Strength

OD (µm)	Outer SiCH 9at% Si (µm)	Inner SCD (µm)	Total Wall (mm)	Buckle Pres. PSI	Youngs Modulus E (Gpa)
819	4.2	2.6	6.8	121	2.44
869	5.6	2.1	7.7	123	2.33

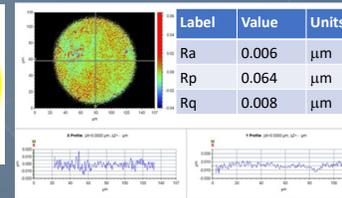
Note: All type 3 and Type 4 capsules tested survived 150 PSI fill pressure



Batch 1 9% SiCH/SCD
Batch 2 9% SiCH/SCD

Interesting future possibilities

Free-standing SiCH capsule at 11at% Si is achievable by Pyro of 7% SiCH to 550C



Record? Thinnest, highest aspect ratio SiCH capsule to date



1750x1.1µm post PAMS



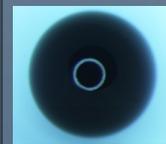
SnO₂ capsule

1280x4µm

Conclusions

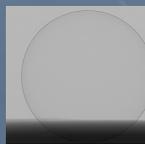
- Methods 3 and 4 (but not 1 or 2) were potentially viable routes for making multi-layered 9at% Si CH capsules.
- Si doped capsules have higher Youngs Modulus than normal CH or SCD capsules.
- 9at% Si SiCH can be deposited with sufficiently smooth surface finish but must be deposited after PAMS pyrolysis step.
- Very thin high aspect ratio SiCH capsules can be made, but can they be handled?
- "Black glass" as possible future replacement for SiO₂ glass? Not transparent but stronger than glass and fillable using standard glass capsule filling process.
- Black glass, high carbon content with much lower silicon and oxygen content than glass.

Possible replacement for glass



8at% SiGeCH pyro'd to 1100C In He

875x3.2 Noir Glass



SigRay x-ray image demonstrating wall uniformity and very high aspect ratio

- 875x3.2 µm; d = 1.95g/cc
- 0.63g/cc Si after pyrolysis
- 0.05g/cc Ge after pyrolysis
- Buckle Pressure ~450PSI
- 10/10 capsules survived 20 atm DD fill
- He HL 2-4hrs
- No residual gas
- Youngs Modulus 50Gpa
- Stronger than conversion glass